

C² 8. (Amended) A silicon wafer, cut from the silicon ingot of claim 7, wherein the inner diameter of the OSF ring is at least 1/2 the inner diameter of the wafer and an oxide film withstand the voltage is 60% or higher at a C mode ratio.

C³ 10. (Amended) A silicon wafer for non-annealing, cut from the silicon ingot of claim 7, wherein the inner diameter of an OSF ring is at least 1/2 a wafer inner diameter and an oxide film withstand voltage is 60% or higher at a C mode ratio.

Please add claim 15 as follows:

C⁴ 15. (New) A method of producing a silicon single crystal ingot of claim 3, wherein $G_{\text{outer}}/G_{\text{center}}$, which is a ratio of values at a crystal outer edge and at a crystal center of an average value G of the temperature gradient in the crystal, within a temperature range from a silicon melting point to 1350°C, is between 1.10 and 1.50. --

REMARKS

In the above-identified Office Action the Examiner has rejected claim 1 under 35 U.S.C. § 112 as well as claims 10, 11 and 14. Applicant has cancelled claims 1 and 11 thereby obviating these rejections. Claim 10 has been amended to eliminate the objected to limitation.

In addition to the above, the Examiner has rejected claims 1-2 and 4-14 as being anticipated by the patent Iida, et al.; these claims, with the exception of claims 7-10, have been cancelled and accordingly need not be commented on further. With regard to claims 7-10, the Examiner stated that Iida teaches a similar silicon ingot as Applicant's ingot of claim 7 and that Iida teaches a silicon ingot pulled by CZ method under conditions similar to Applicant.